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source are mixed together to thereby generate light different in luminescent color from the light emitted from said primary light source, and

wherein the GaN semiconductor light-emitting device comprises:

a substrate;

a light-emitting layer configured to emit light and positioned a first distance from the substrate; and

a reflection layer configured to reflect light toward a light extracting direction and being positioned a second distance from the substrate, wherein the second distance is less than the first distance so that the reflection layer is positioned closer to the substrate than the light-emitting layer.

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11. (Twice Amended) A light-emitting apparatus comprising:

a primary light source including a GaN semiconductor light-emitting device with an emission wavelength of from 420 nm to 490 nm;

a secondary light source including a first fluorescent material composed of at least one member selected from the group consisting of ZnS:Eu, YVO<sub>4</sub>:Ce and Y<sub>2</sub>O<sub>2</sub>S:Ce; and

a third light source including a second fluorescent material configured to absorb the light of said primary light source, the third light source being configured to emit red light,

wherein said secondary light source emits light based on light given from said primary light source so that light of said secondary light source and the light of said primary light source are mixed together to thereby generate light different in luminescent color from the light emitted from said primary light source, and

wherein the GaN semiconductor light-emitting device comprises:

a substrate;

a light-emitting layer configured to emit light and positioned a first distance from the substrate; and

a reflection layer configured to reflect light toward a light extracting direction and being positioned a second distance from the substrate, wherein the second distance is less than the first distance so that the reflection layer is positioned closer to the substrate than the light-emitting layer.

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21. (Twice Amended) A light-emitting apparatus comprising:  
a first light source including a GaN semiconductor light-emitting device configured to emit blue light;  
a second light source including a first fluorescent material configured to absorb light of said first light source and to emit green light; and  
a third light source comprising a red color LED configured to emit red light;  
wherein the light of said first light source, light of said second light source and light of said third light source are mixed together to thereby generate white light, and  
wherein the GaN semiconductor light-emitting device comprises:  
a substrate;  
a light-emitting layer configured to emit light and positioned a first distance from the substrate; and  
Sub C3  
a reflection layer configured to reflect light toward a light extracting direction and being positioned a second distance from the substrate, wherein the second distance is less than the first distance so that the reflection layer is positioned closer to the substrate than the light-emitting layer.

22. (Twice Amended) A light-emitting apparatus according to claim 21, wherein said first fluorescent material is composed of at least one member selected from the group consisting of ZnS:Cu, Au, Al; ZnS:Cu; ZnS:Eu; YVO<sub>4</sub>:Ce; and Y<sub>2</sub>O<sub>2</sub>S:Ce.

23. (Amended) A light-emitting apparatus comprising:  
a first light source including a GaN semiconductor light-emitting device configured to emit blue light;  
a second light source including a first fluorescent material configured to absorb light of said primary light source and configured to emit green light; and  
a third light source including a second fluorescent material configured to absorb light of said first light source and configured to emit red light,  
wherein light of said first light source, light of said second light source and light of said third light source are mixed together to thereby generate white light.

35. (Amended) A light-emitting apparatus comprising:  
a primary light source including a GaN semiconductor light-emitting device with an emission wavelength of from 420 nm to 490 nm;  
a secondary light source including a first fluorescent material composed of at least one member selected from the group consisting of ZnS:Cu; Au, Al; ZnS:Cu; ZnS:Mn; ZnS:Eu; YVO<sub>4</sub>:Eu; YVO<sub>4</sub>:Ce; Y<sub>2</sub>O<sub>2</sub>S:Eu and Y<sub>2</sub>O<sub>2</sub>S:Ce; and  
a third light source including a second fluorescent material configured to absorb the light of said primary light source, the third light source being configured to emit red light,  
wherein said secondary light source emits light based on light given from said primary light source so that light of said secondary light source and the light of said primary light source are mixed together to thereby generate light different in luminescent color from the light emitted from said primary light source.

**Please see the attached Appendix for the changes made to effect the above claims.**